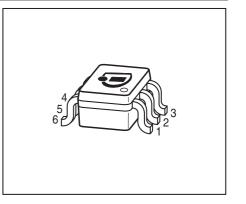


BFS17S

NPN Silicon RF Transistor

- For broadband amplifiers up to 1 GHz at collector currents from 1 mA to 20 mA
- BFS17S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration						Package
BFS17S	MCs	1=B1	2=E1	3=C2	4=B2	5=E2	6=C1	SOT363

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V _{CEO}	15	V
Collector-base voltage	V _{CBO}	25	
Emitter-base voltage	V _{EBO}	2.5	
Collector current	I _C	25	mA
Peak collector current, $f = 10 \text{ MHz}$	I _{CM}	50	
Total power dissipation ¹⁾	P _{tot}	280	mW
<i>T</i> _S ≤ 93 °C			
Junction temperature	TJ	150	°C
Ambient temperature	T _A	-65 150	
Storage temperature	T _{Sta}	-65 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 240	K/W

 $^{1}T_{S}$ is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB}$ = 10 V, $I_{\rm E}$ = 0		-	-	0.05	
$V_{\rm CB}$ = 25 V, $I_{\rm E}$ = 0		-	-	10	
Emitter-base cutoff current	I _{EBO}	-	-	100	
$V_{\rm EB}$ = 2.5 V, $I_{\rm C}$ = 0					
DC current gain	h _{FE}				-
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 1 V, pulse measured		40	-	150	
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 1 V, pulse measured		20	70	-	
Collector-emitter saturation voltage	V _{CEsat}	-	0.1	0.4	V
<i>I</i> _C = 10 mA, <i>I</i> _B = 1 mA					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified



Parameter	Symbol		Unit		
		min.	typ.	max.	
AC Characteristics (verified by random sam	pling)		1	1	
Transition frequency	f _T				GHz
<i>I</i> _C = 2 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 200 MHz		1	1.4	-	
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 5 V, f = 200 MHz		1.3	2.5	-	
Collector-base capacitance	C _{cb}	-	0.55	0.8	pF
$V_{\rm CB}$ = 5 V, f = 1 MHz, $V_{\rm BE}$ = 0 ,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.2	-	
$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.9	1.45	
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,					
collector grounded					
Minimum noise figure	NF _{min}	-	3	5	dB
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 5 V, $Z_{\rm S}$ = 50 Ω ,					
<i>f</i> = 800 MHz					
Transducer gain	S _{21e} ²	-	14	-	dB
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 5 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 500 MHz					
Third order intercept point at output	IP ₃	-	22.5	-	dBm
V _{CE} = 5 V, <i>I</i> _C = 20 mA, <i>f</i> = 800 MHz,					
$Z_{\rm S} = Z_{\rm Sopt}, Z_{\rm L} = Z_{\rm Lopt}$					
1dB compression point	P _{-1dB}	-	11	-	-
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 5 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 800 MHz					
		1	1	1	1

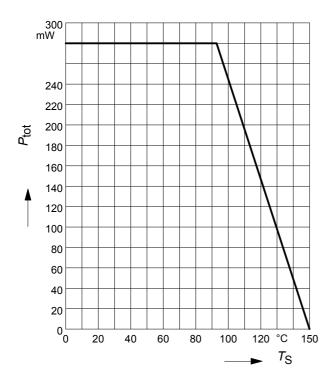
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified



BFS17S

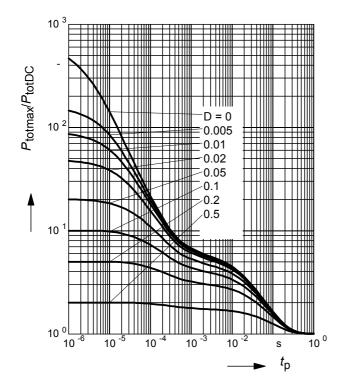
Total power dissipation $P_{tot} = f(T_S)$

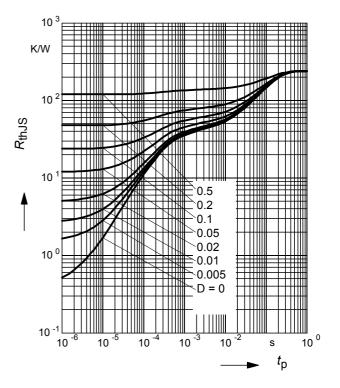
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



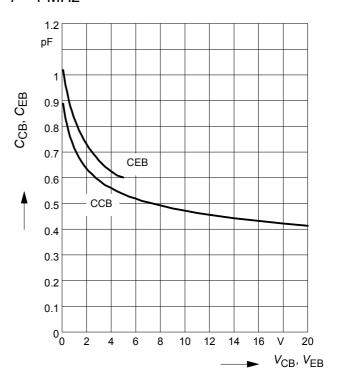
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$





Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$ f = 1 MHz

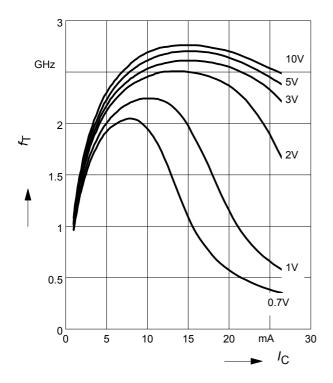




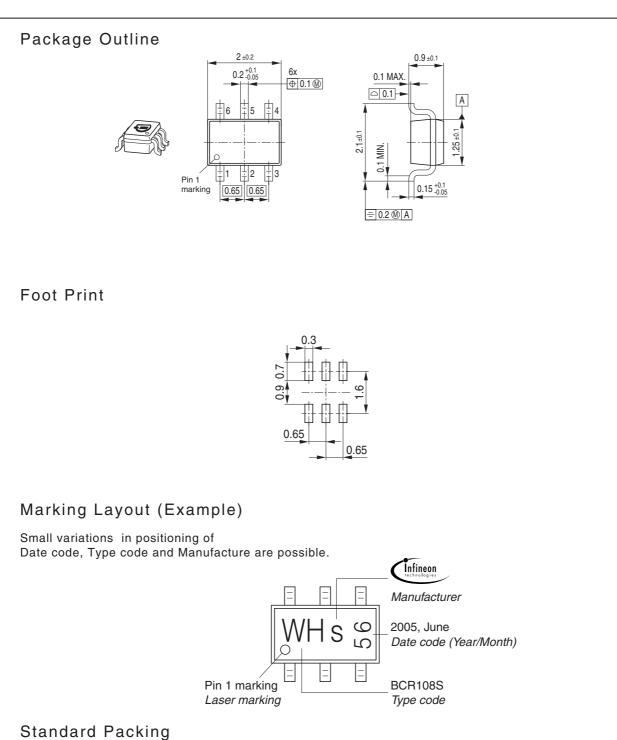
BFS17S

Transition frequency $f_{T} = f(I_{C})$

 V_{CE} = parameter

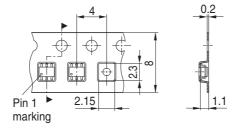






Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.







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